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UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,833,314 B2
DATED : December 21, 2004
INVENTOR(S) : Maleville et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page,

Item [56], **References Cited**, OTHER PUBLICATIONS,

"Shiettekatte et al." reference, delete "Shiettekatte" and insert -- Schiettekatte --; after "temperature influence", insert -- on --; and after "extended defects", delete "nucleanon" and insert -- nucleation --.

"L.J. Huang et al." reference, after "Model for blistering", insert -- and splitting --.

"Bruel et al." reference, after "Nuclear", delete "instrument" and insert -- instruments --.

"Lanzieri et al." reference, delete "semi-insulating Gaas" and insert -- semi-insulating GaAs --

Insert the following reference:

-- da Silva et al., "The effects of implantation temperature on He bubble formation in silicon," Nuclear Instruments and Methods in Physics Research Section B: Beam Interactions with Materials and Atoms, Vols. 175-177, pp. 335-339 (April 2001). --.

Item [57], **ABSTRACT**,

Line 5, after "implanted atomic species to", delete "from" and insert -- form --.

Column 9,

Line 55, before "blisters in a surface region", delete "from" and insert -- form --.

Column 10,

Line 53, after "that is implanted comprises hydrogen", delete "of" and insert -- or --.

Signed and Sealed this

First Day of March, 2005



JON W. DUDAS
Director of the United States Patent and Trademark Office